



60V PNP MEDIUM POWER TRANSISTOR IN SOT23

Features

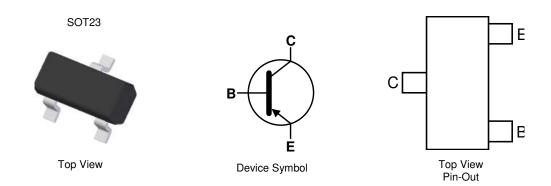
- BV_{CEO} > -60V
- I_C = -4A High Continuous Collector Current
- I_{CM} = -10A Peak Pulse Current
- Low Saturation Voltage -60mV Max @ I_C = -1A.
- $R_{CE(SAT)} = 45m\Omega$ at 1A for a Low Equivalent On-Resistance
- 1.2W Power Dissipation
- Complimentary NPN Type: ZXTN2018F
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 63
- Weight 0.008 grams (Approximate)

Application

- Gate Driving MOSFETs and IGBTs
- Motor Drive
- Relay, Lamp and Solenoid Drive
- High Side Switches



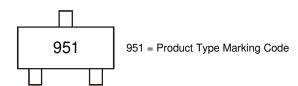
Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZXTP2027FTA	951	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information





Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-100	V
Collector-Emitter Voltage	V_{CEV}	-100	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-7	V
Peak Pulse Collector Current	I _{CM}	-10	Α
Continuous Collector Current	Ic	-4	Α
Base Current	l _Β	-1	А

Thermal Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	1.0	W
Power Dissipation (Note 6)	P _D	1.2	W
Power Dissipation (Note 7)	P _D	1.56	W
Thermal Resistance, Junction to Ambient Air (Note 5)	$R_{\theta JA}$	125	°C/W
Thermal Resistance, Junction to Ambient Air (Note 6)	$R_{\theta JA}$	104	°C/W
Thermal Resistance, Junction to Ambient Air (Note 7)	$R_{\theta JA}$	80	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 5. For a device mounted with the collector lead on 18mm x 18mm 2oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.

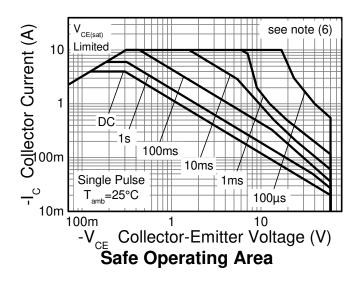
 6. Same as note (5), except the device is mounted on 30mm x 30mm 2oz copper.

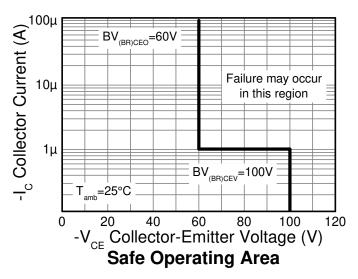
 7. Same as note (6), except measured at t<5secs.

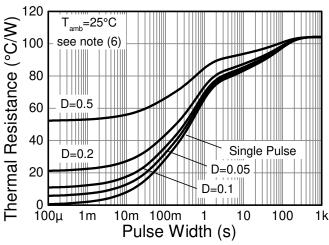
 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

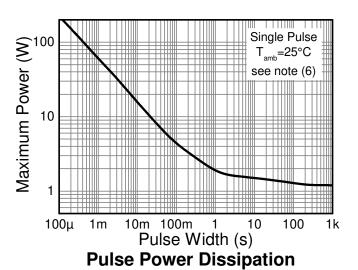


Thermal Characteristics and Derating Information









Transient Thermal Impedance

Mod Not 1.2 | See note (6) | See note (6) | See note (5) | See note (6) | See not

Derating Curve



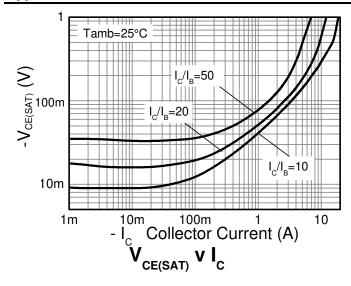
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

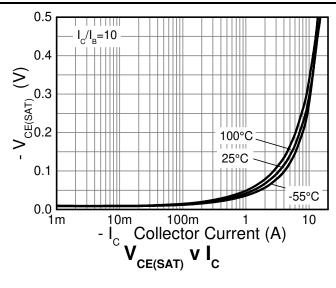
Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage		-100	-120	_	V	$I_C = -100\mu A$
Collector-Emitter Breakdown Voltage		-100	-120	_	V	$I_C = -1 \mu A, \ 1V > V_{BE} > -0.3V$
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	-60	-75	_	V	$I_C = -10mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	-7.0	-8.2	_	V	$I_E = -100\mu A$
Collector-Emitter Cutoff Current	I _{CEV}	_		-20	nA	$V_{CE} = -80V$, $V_{BE} = 1V$
Collector-Base Cutoff Current	I _{CBO}	_		-20	nA	$V_{CB} = -80V, I_E = 0$
Emitter-Base Cutoff Current	I _{EBO}	_	_	-10	nA	$V_{EB} = -6V, I_C = 0$
ON CHARACTERISTICS (Note 9)						
		100	250	_		$V_{CE} = -2V$, $I_C = -10mA$
DC Current Gain	h	100	200	300		$V_{CE} = -2V$, $I_C = -2A$
DO Guitent Gain	h _{FE}	80	145	_	_	$V_{CE} = -2V$, $I_C = -4A$
		20	40	_		$V_{CE} = -2V$, $I_{C} = -10A$
		_	-15	-25	mV	$I_C = -100 \text{mA}, I_B = -10 \text{mA}$
Collector-Emitter Saturation Voltage	V	_	-45	-60		$I_C = -1A$, $I_B = -100mA$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	-70	-95		$I_C = -2A$, $I_B = -200mA$
		_	-155	-240		$I_C = -4A$, $I_B = -200mA$
Base-Emitter Saturation Voltage	V _{BE(SAT)}	_	-0.89	-1.0	V	I _C = -4A, I _B = -200mA
Base-Emitter Turn-On Voltage	$V_{BE(ON)}$	_	-0.81	-0.95	V	$V_{CE} = -2V$, $I_C = -4A$
SMALL SIGNAL CHARACTERISTICS						
	t_{D}	_	12.6	_	ns	
Switching times	t _R	_	10.2	_		$V_{CC} = -10V,$ $I_{C} = -2A,$
Owitering times		_	220	_		$I_{C} = -2A$, $I_{B1} = I_{B2} = -200 \text{mA}$
	t _F	_	21	_		J. 3L
Transition Frequency	f _T	_	165		MHz	$V_{CE} = -10V, I_{C} = -100mA,$ f = 50MHz
Output Capacitance	C _{OBO}	_	44	_	pF	V _{CB} = -10V, f = 1MHz

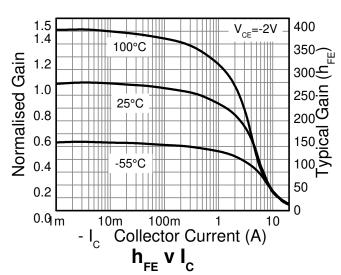
Note: 9. Measured under pulsed conditions. Pulse width $\leq 300\mu s$. Duty cycle $\leq 2\%$.

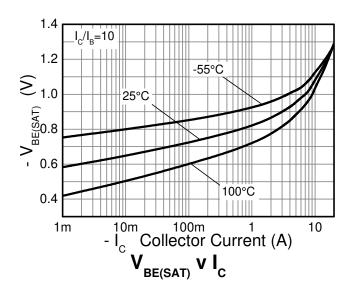


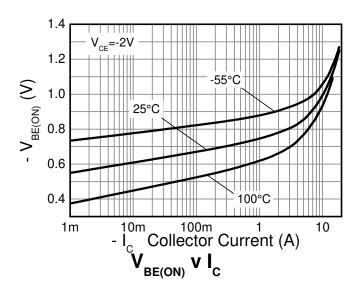
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)









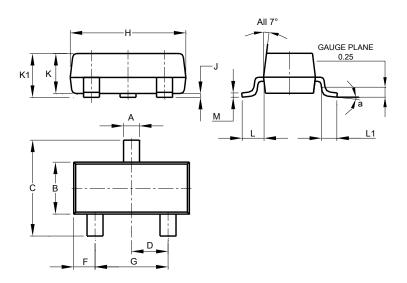




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

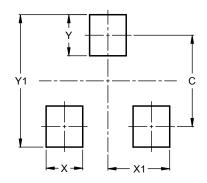


SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.890	1.00	0.975		
K1	0.903	1.10	1.025		
L	0.45	0.61	0.55		
L1	0.25	0.55	0.40		
М	0.085	0.150	0.110		
а	0°	8°			
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)			
С	2.0			
X	0.8			
X1	1.35			
Υ	0.9			
Y 1	2.9			



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